

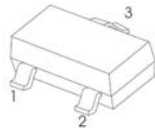


FEATURE

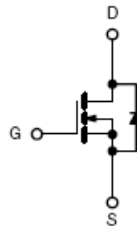
- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

SOT-23

1. GATE
2. SOURCE
3. DRAIN

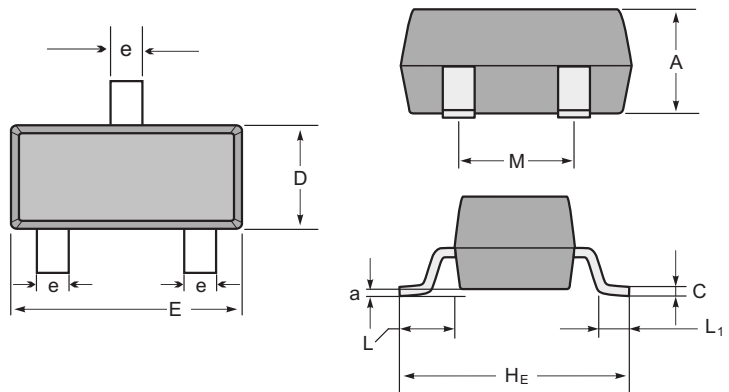


Equivalent Circuit



Marking

Type number	Marking code
SI2300	2300



SOT-23 mechanical data

UNIT	A	C	D	E	H _E	e	M	L	L ₁	a	
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	6	A
Pulsed Drain Current	I_{DM}	25	
Maximum Body-Diode Continuous Current	I_S	2	
Maximum Power Dissipation	P_D	1.25	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	

SI2300

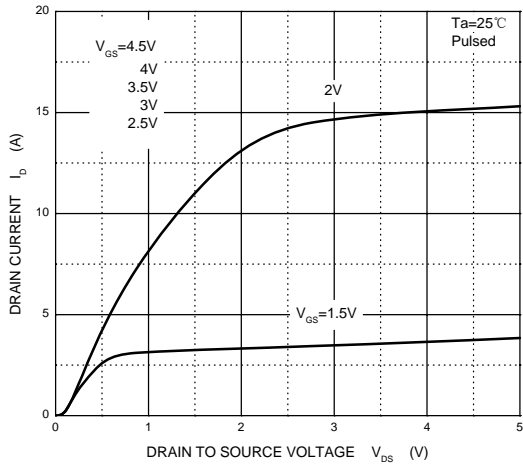
$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Gate-source leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 12V$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 16V, V_{GS} = 0V$			1.0	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	0.7	1.0	V
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 5.0A$		22	27	m Ω
		$V_{GS} = 2.5V, I_D = 4.0A$		35	42	
		$V_{GS} = 1.8V, I_D = 2.0A$			73	
Diode forward voltage	V_{SD}	$V_{GS} = 0V, I_S = 1A$		0.75	1	V
Forward transconductance	g_{fs}	$V_{DS} = 5V, I_D = 3.8A$	4			S
DYNAMIC PARAMETERS*						
Input capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		630		pF
Output capacitance	C_{oss}			164		
Reverse transfer capacitance	C_{rss}			137		
Gate resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.5		Ω
SWITCHING PARAMETERS*						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 5V, V_{DS} = 10V,$ $R_L = 1.7\Omega, R_{GEN} = 6\Omega$		5.5		ns
Rise time	t_r			14		
Turn-off delay time	$t_{d(off)}$			29		
Fall time	t_f			10.2		

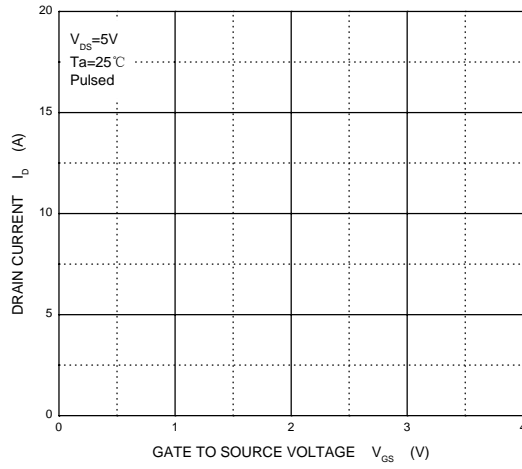
*These parameters have no way to verify.

RATING AND CHARACTERISTIC CURVES (SI2300)

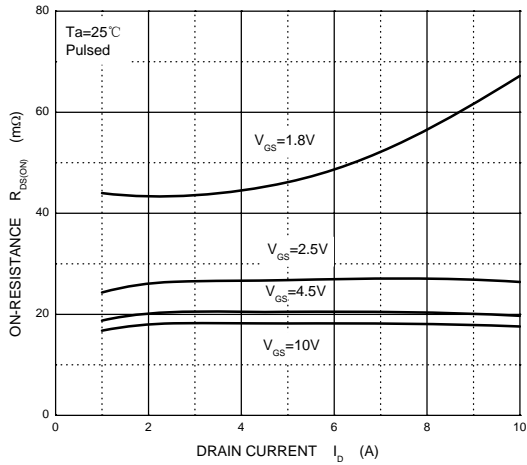
Output Characteristics



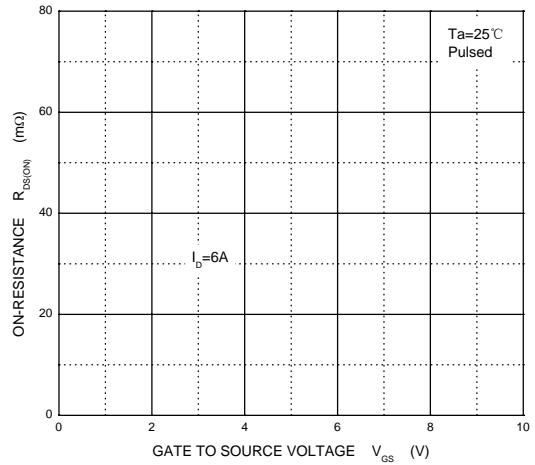
Transfer Characteristics



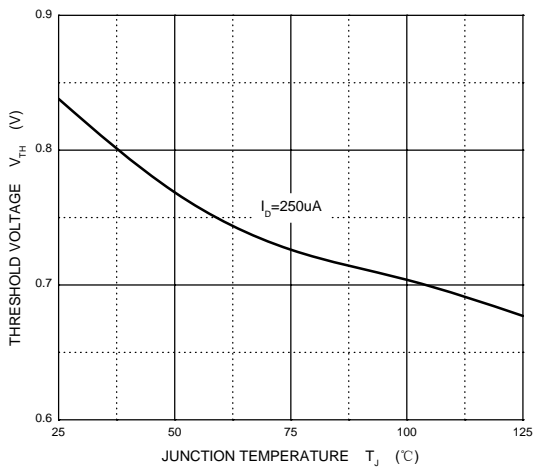
$R_{DS(ON)}$ — I_D



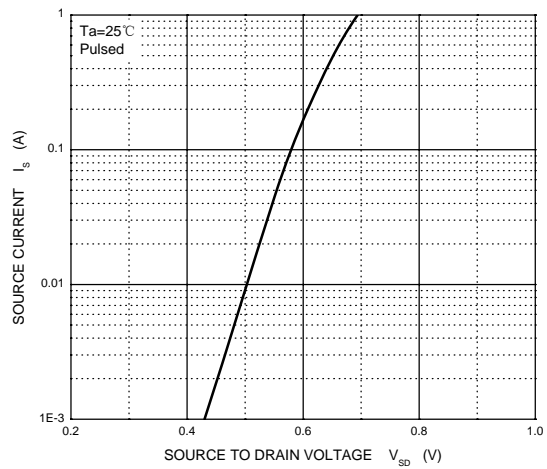
$R_{DS(ON)}$ — V_{GS}



Threshold Voltage



I_S — V_{SD}



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